Icemos Technology Ltd **Product Specification** **1000.769701** Issue Date 24 February 2025 05:

Part Number Customer

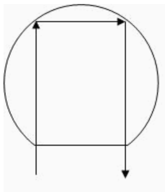
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	semi std/none	
	5.0	Overall Thickness	728.00 +/- 17.00 µm	ADE 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20% Best effort not guaranteed
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20% Best effort not guaranteed
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	550.00 +/- 15.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	<=0.01 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with laser mark and oxide.	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	30,000.00 +/- 3,000.00 A	Nanospec centre point, 4%
DeviceSilicon	20.0	Device Growth Method	CZ	Wafer Vendor
	21.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	22.0	Nominal Thickness	175.00 +/- 1.00 µm	ADE Single Point, 100%
	23.0	Device Doping Type	P	Wafer Vendor
	24.0	Device Dopant	Boron	Wafer Vendor
	25.0	Device Resistivity	<=0.01 Ohmcm	Wafer Vendor
	26.0	Voids	0	Bright Light, 100% (note 2)
	27.0	Scratches	0	Bright Light, 100% (note 2)
	28.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

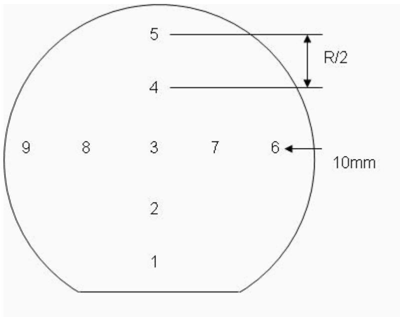
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information